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Kind regards,

Team Nexperia

# PEMD48; PUMD48

NPN/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$  and R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

Rev. 6 — 24 January 2012

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	Package	
	NXP	JEITA	configuration
PEMD48	SOT666	-	ultra small and flat lead
PUMD48	SOT363	SC-88	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transisto	or; for the PNP transistor	with negative polarity				
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
<b>Transistor T</b>	R1 (NPN)					
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		8.0	1.0	1.2	
<b>Transistor T</b>	R2 (PNP)					
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



### 2. Pinning information

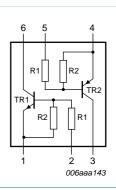
Table 3. Pinning

Table 3.	Filling		
Pin	Description	Simplified outline	Graphic symbol
PEMD48	(SOT666)		
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2	1 2 3	TR1
6	output (collector) TR1	1 2 3	R2 R1
			1 2 3 006aaa143
			000000170

#### **PUMD48 (SOT363)**

1	GND (emitter) TR1
2	input (base) TR1
3	output (collector) TR2
4	GND (emitter) TR2
5	input (base) TR2
6	output (collector) TR1





## 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMD48	-	plastic surface-mounted package; 6 leads	SOT666	
PUMD48	SC-88	plastic surface-mounted package; 6 leads	SOT363	

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD48	48
PUMD48	4*8

[1] \* = placeholder for manufacturing site code.

## 5. Limiting values

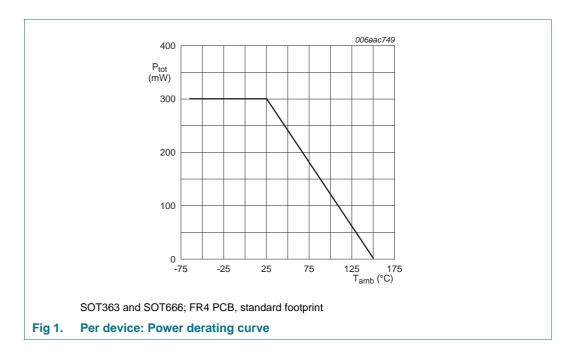
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

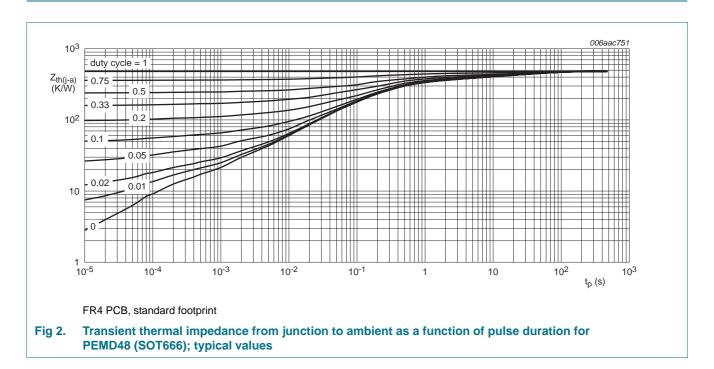
Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pola	rity		
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector			
	TR1 (NPN)		-	10	V
	TR2 (PNP)		-	-5	V
VI	input voltage TR1				
	positive		-	+40	V
	negative		-	-10	V
	input voltage TR2				
	positive		-	+5	V
	negative		-	-12	V
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$			
	PEMD48 (SOT666)		[1][2] _	200	mW
	PUMD48 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMD48 (SOT666)		[1][2] _	300	mW
	PUMD48 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



### 6. Thermal characteristics



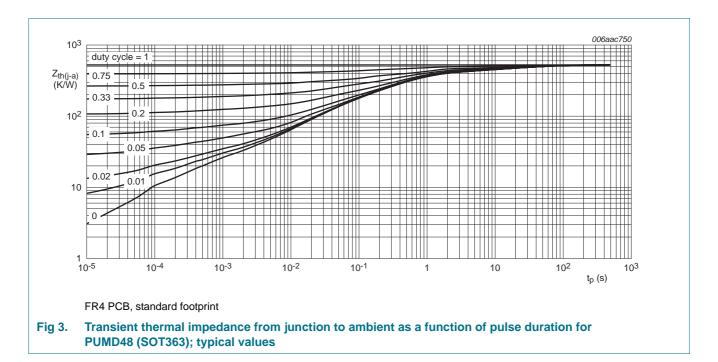


Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25  ^{\circ}C$				
	PEMD48 (SOT666)		[1][2]	-	625	K/W
	PUMD48 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	)					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25  ^{\circ}C$				
	PEMD48 (SOT666)		[1][2] _	-	417	K/W
	PUMD48 (SOT363)		<u>[1]</u> -	-	417	K/W
	•					

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

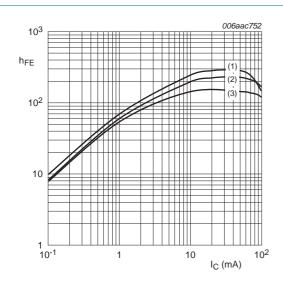
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	istor; for the PNP trans	istor with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$		-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$		-	-	5	μΑ
Transisto	r TR1 (NPN)						
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	90	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$		80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$		-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$		-	1.2	8.0	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$		3	1.6	-	V
R1	bias resistor 1 (input)			33	47	61	kΩ
R2/R1	bias resistor ratio			0.8	1.0	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CB} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1]	-	230	-	MHz
Transisto	r TR2 (PNP)						
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$		-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$		-	-0.6	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$		-1.1	-0.75	-	V
R1	bias resistor 1 (input)			1.54	2.20	2.86	$k\Omega$
R2/R1	bias resistor ratio			17	21	26	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CB} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	[1]	-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor.



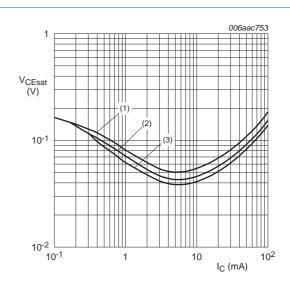
$$V_{CE} = 5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. TR1 (NPN): DC current gain as a function of collector current; typical values



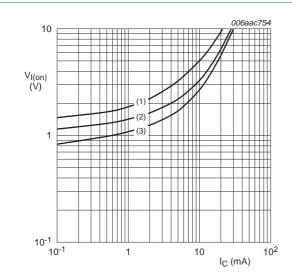
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



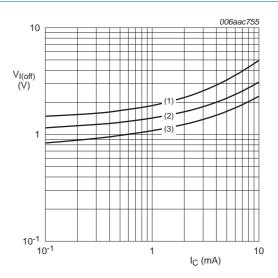


(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 6. TR1 (NPN): On-state input voltage as a function of collector current; typical values



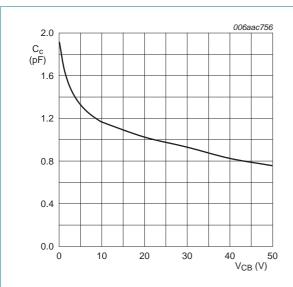
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

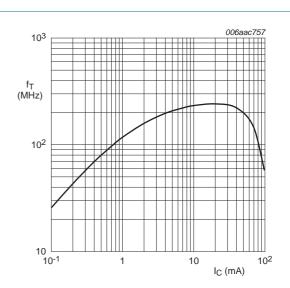
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



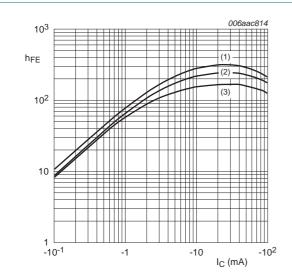
f = 1 MHz; T<sub>amb</sub> = 25 °C

Fig 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

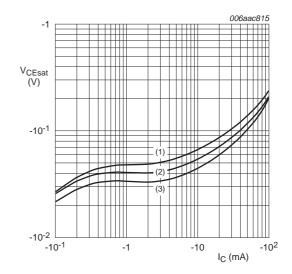
Fig 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 25 °C
- (3)  $T_{amb} = -40 \, ^{\circ}C$

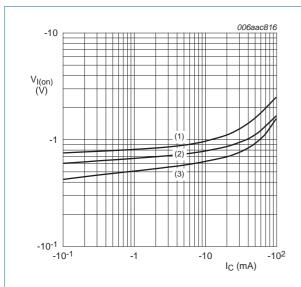
Fig 10. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 11. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 12. TR2 (PNP): On-state input voltage as a function of collector current; typical values

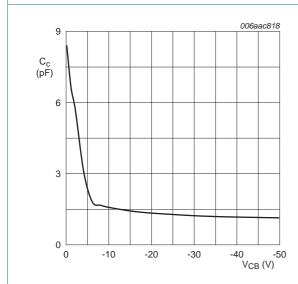
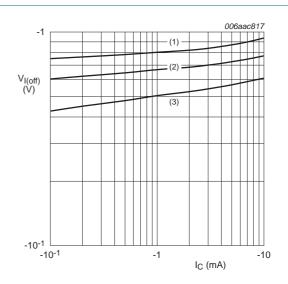


Fig 14. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 



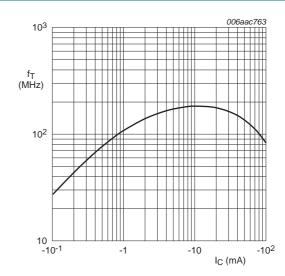
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 13. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$ 

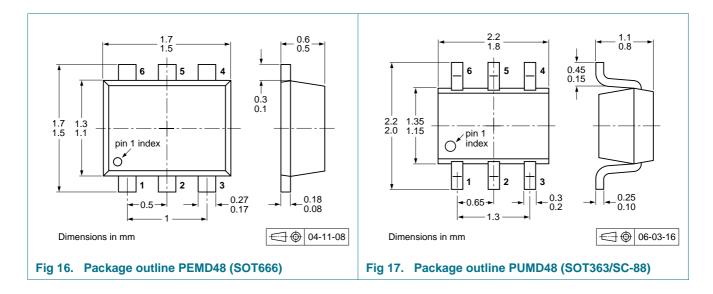
Fig 15. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



### 10. Packing information

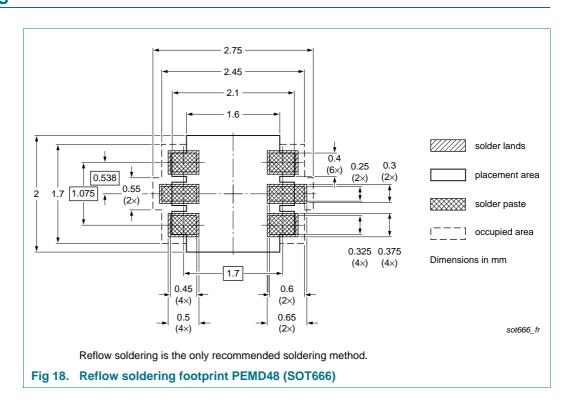
Table 9. Packing methods

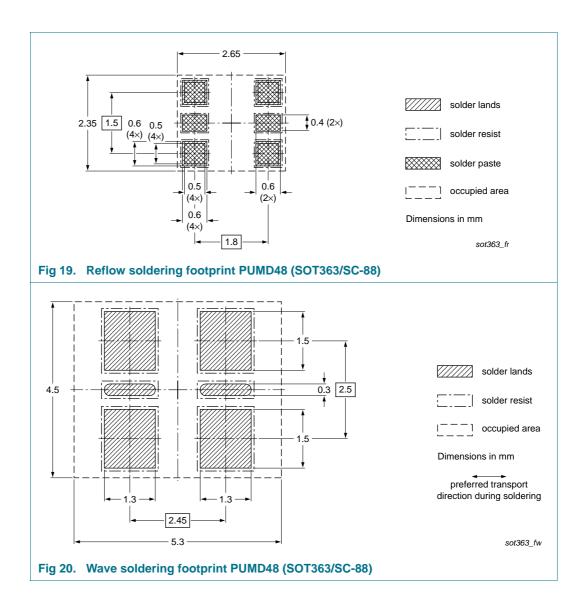
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре			Packir	Packing quantity			
number			3000	4000	8000	10000	
PEMD48	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-	-115	-	-	
PUMD48	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165	

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

### 11. Soldering





## 12. Revision history

Table 10. Revision history

Tubic for the vicion files	,			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD48_PUMD48 v.6	20120124	Product data sheet	-	PEMD48_PUMD48 v.5
Modifications:	<ul> <li>Section 1 "Product profile": updated</li> <li>Section 4 "Marking": updated</li> <li>Table 7 "Thermal characteristics": updated according to the latest measurements</li> <li>Table 6 "Limiting values": updated according to the latest measurements</li> <li>Table 8 "Characteristics": I<sub>CEO</sub> updated according to the latest measurements, f<sub>T</sub> added</li> <li>Figure 1 to 3, 8, 9, 14 and 15: added</li> <li>Figure 4 to 7 and Figure 10 to 13: updated</li> <li>Section 8 "Test information": added</li> <li>Section 11 "Soldering": added</li> <li>Section 13 "Legal information": updated</li> </ul>			
PEMD48_PUMD48 v.5	20100413	Product data sheet	-	PEMD48_PUMD48 v.4
PEMD48_PUMD48 v.4	20040624	Product specification	-	PEMD48_PUMD48 v.3
PEMD48_PUMD48 v.3	20040602	Product specification	-	PEMD48 v.2 PUMD48 v.2
PUMD48 v.2	20010201	Product specification		PUMD48 v.1
PUMD48 v.1	19990422	Product specification		-
PEMD48 v.2	20011107	Product specification		PEMD48 v.1
PEMD48 v.1	20010924	Preliminary specification	on -	-

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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PEMD48\_PUMD48

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## PEMD48; PUMD48

### **NPN/PNP** resistor-equipped transistors

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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For sales office addresses, please send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

### 15. Contents

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